

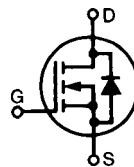
# High Current MegaMOS™FET

**IXTK 33N50**

$$\begin{aligned} V_{DSS} &= 500 \text{ V} \\ I_{D(\text{cont})} &= 33 \text{ A} \\ R_{DS(\text{on})} &= 0.17 \Omega \end{aligned}$$

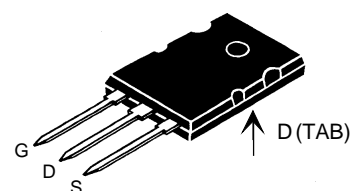
## N-Channel Enhancement Mode

Preliminary data



Symbol	Test conditions	Maximum ratings	
$V_{DSS}$	$T_J = 25^\circ\text{C to } 150^\circ\text{C}$	500	V
$V_{DGR}$	$T_J = 25^\circ\text{C to } 150^\circ\text{C}; R_{GS} = 1.0 \text{ M}\Omega$	500	V
$V_{GS}$	Continuous	$\pm 20$	V
$V_{GSM}$	Transient	$\pm 30$	V
$I_{D25}$	$T_C = 25^\circ\text{C}$	33	A
$I_{DM}$	$T_C = 25^\circ\text{C}$ , pulse width limited by $T_{JM}$	132	A
$P_D$	$T_C = 25^\circ\text{C}$	416	W
$T_J$		-55 ... +150	$^\circ\text{C}$
$T_{JM}$		150	$^\circ\text{C}$
$T_{stg}$		-55 ... +150	$^\circ\text{C}$
$M_d$	Mounting torque	1.13/10	Nm/lb.in.
<b>Weight</b>		10	g
Max lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	$^\circ\text{C}$

TO-264 AA



G = Gate  
S = Source

D = Drain  
TAB = Drain

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
$V_{DSS}$	$V_{GS} = 0 \text{ V}, I_D = 5 \text{ mA}$ BV <sub>DSS</sub> temperature coefficient	500	0.087	%/K
$V_{GS(\text{th})}$	$V_{DS} = V_{GS}, I_D = 250 \mu\text{A}$ $V_{GS(\text{th})}$ temperature coefficient	2.0	-0.25	%/K
$I_{GSS}$	$V_{GS} = \pm 20 \text{ V DC}, V_{DS} = 0$			$\pm 100 \text{ nA}$
$I_{DSS}$	$V_{DS} = 0.8 V_{DSS}$ $V_{GS} = 0 \text{ V}$			$200 \mu\text{A}$ $3 \text{ mA}$
$R_{DS(\text{on})}$	$V_{GS} = 10 \text{ V}, I_D = 0.5 I_{D25}$			0.17 $\Omega$

### Features

- Low  $R_{DS(\text{on})}$  HDMOS™ process
- Rugged polysilicon gate cell structure
- International standard package
- Fast switching times

### Applications

- Motor controls
- DC choppers
- Uninterruptable Power Supplies (UPS)
- Switch-mode and resonant-mode

### Advantages

- Easy to mount with one screw (isolated mounting screw hole)
- Space savings
- High power density

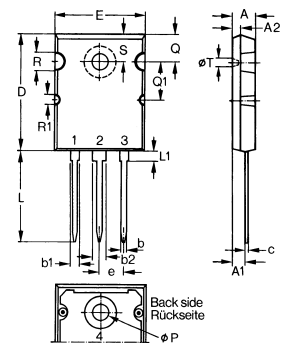
Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ unless otherwise specified)	Characteristic values		
		Min.	Typ.	Max.
$g_{fs}$	$V_{DS} = 10\text{ V}; I_D = 0.5 I_{D25}$ , pulse test		24	S
$C_{iss}$	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		4900	pF
$C_{oss}$			690	pF
$C_{rss}$			300	pF
$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 V_{DSS}, I_D = 0.5 I_{D25}$ $R_G = 1\ \Omega$ (External)		53	ns
$t_r$			30	ns
$t_{d(off)}$			140	ns
$t_f$			40	ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 V_{DSS}, I_D = 0.5 I_{D25}$		250	nC
$Q_{gs}$			30	nC
$Q_{gd}$			115	nC
$R_{thJC}$				0.30 K/W
$R_{thCK}$			0.15	K/W

### Source-Drain Diode

### Ratings and Characteristics ( $T_J = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Test Conditions	Min.	Typ.	Max.
$I_S$	$V_{GS} = 0\text{ V}$			33 A
$I_{SM}$	Repetitive; pulse width limited by $T_{JM}$			132 A
$V_{SD}$	$I_F = I_S, V_{GS} = 0\text{ V},$ Pulse test, $t \leq 300\ \mu\text{s}$ , duty cycle $d \leq 2\%$			1.5 V
$t_{rr}$	$I_F = I_S, -di/dt = 100\text{ A}/\mu\text{s}, V_R = 100\text{ V}$		850	ns

### TO-264 AA Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.82	5.13	.190	.202
A1	2.54	2.89	.100	.114
A2	2.00	2.10	.079	.083
b	1.12	1.42	.044	.056
b1	2.39	2.69	.094	.106
b2	2.90	3.09	.114	.122
c	0.53	0.83	.021	.033
D	25.91	26.16	1.020	1.030
E	19.81	19.96	.780	.786
e	5.46 BSC		.215 BSC	
J	0.00	0.25	.000	.010
K	0.00	0.25	.000	.010
L	20.32	20.83	.800	.820
L1	2.29	2.59	.090	.102
P	3.17	3.66	.125	.144
Q	6.07	6.27	.239	.247
Q1	8.38	8.69	.330	.342
R	3.81	4.32	.150	.170
R1	1.78	2.29	.070	.090
S	6.04	6.30	.238	.248
T	1.57	1.83	.062	.072

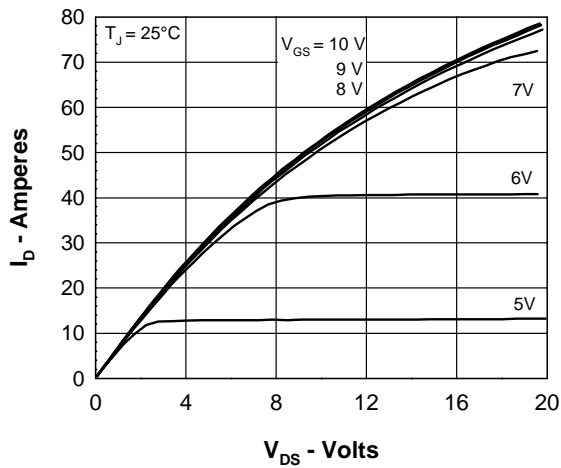


Figure 1. Output Characteristics at 25°C

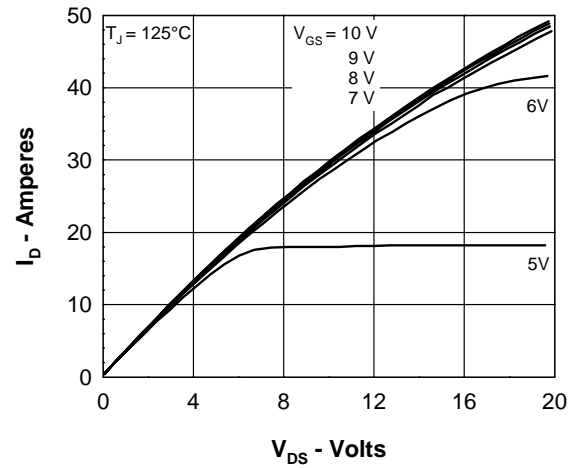


Figure 2. Output Characteristics at 125°C

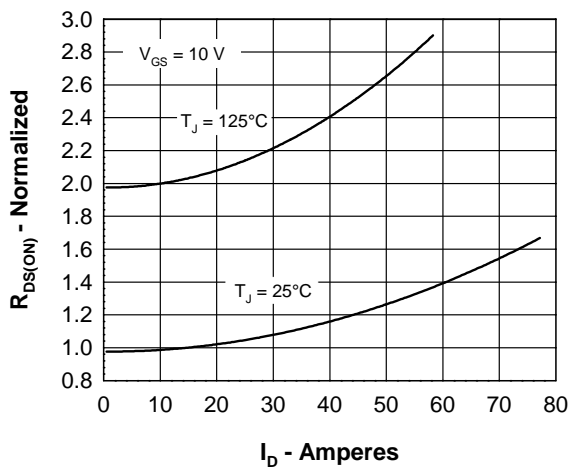
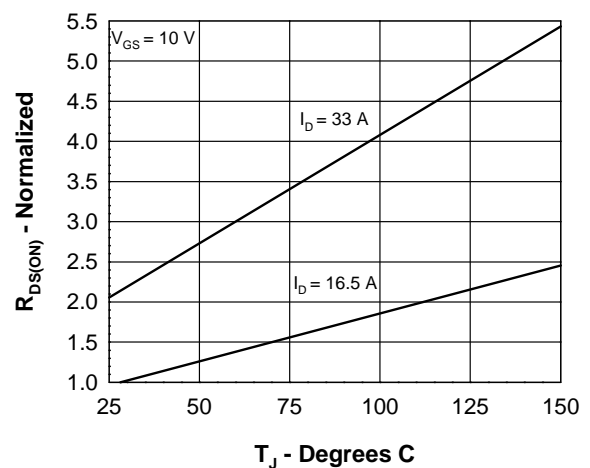
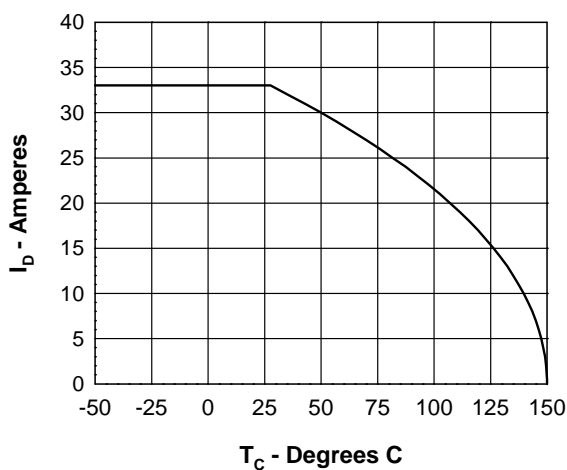

Figure 3.  $R_{DS(on)}$  normalized to 16.5A/25°C vs.  $I_D$ 

Figure 4.  $R_{DS(on)}$  normalized to 16.5A/25°C vs.  $T_J$ 


Figure 5. Drain Current vs. Case Temperature

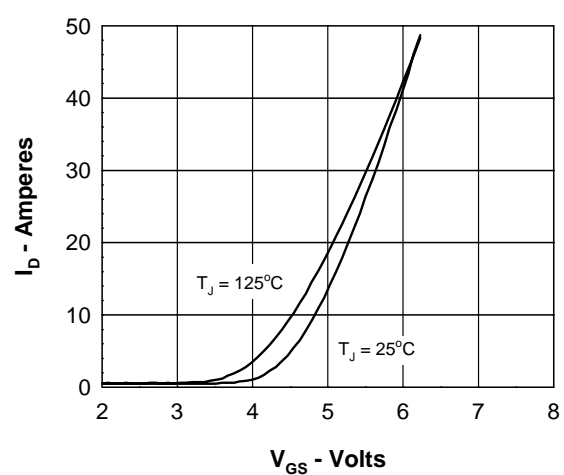


Figure 6. Admittance Curves

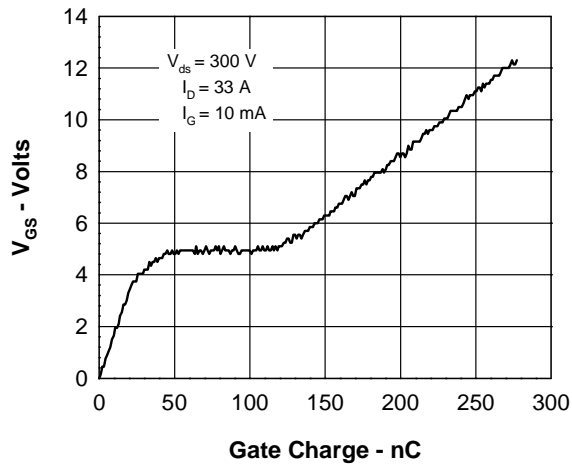


Figure 7. Gate Charge

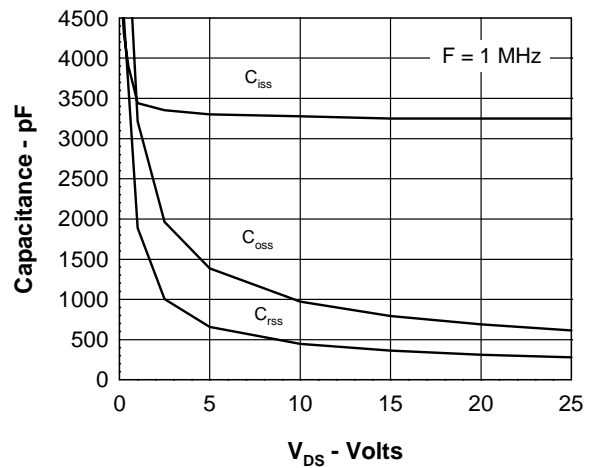


Figure 8. Capacitance Curves

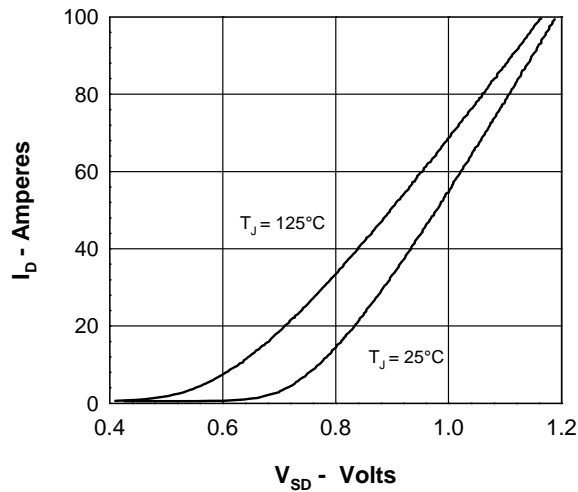


Figure 9. Source Current vs. Source-to-Drain Voltage

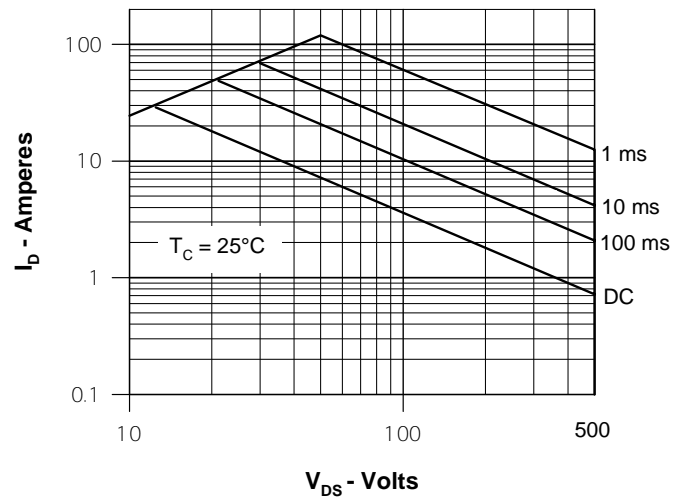


Figure 10. Forward Biased SOA

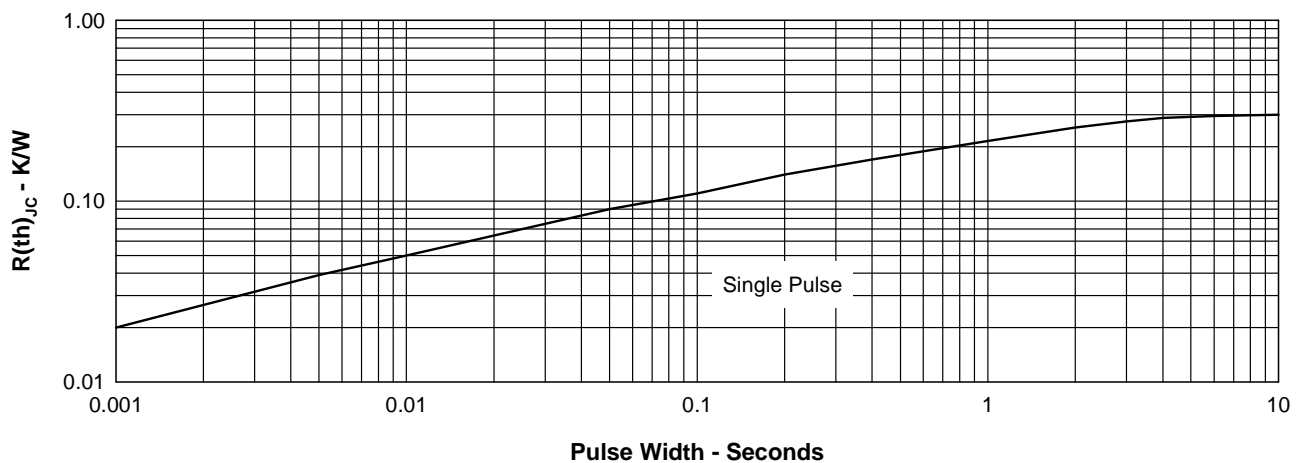


Figure 11. Transient Thermal Resistance